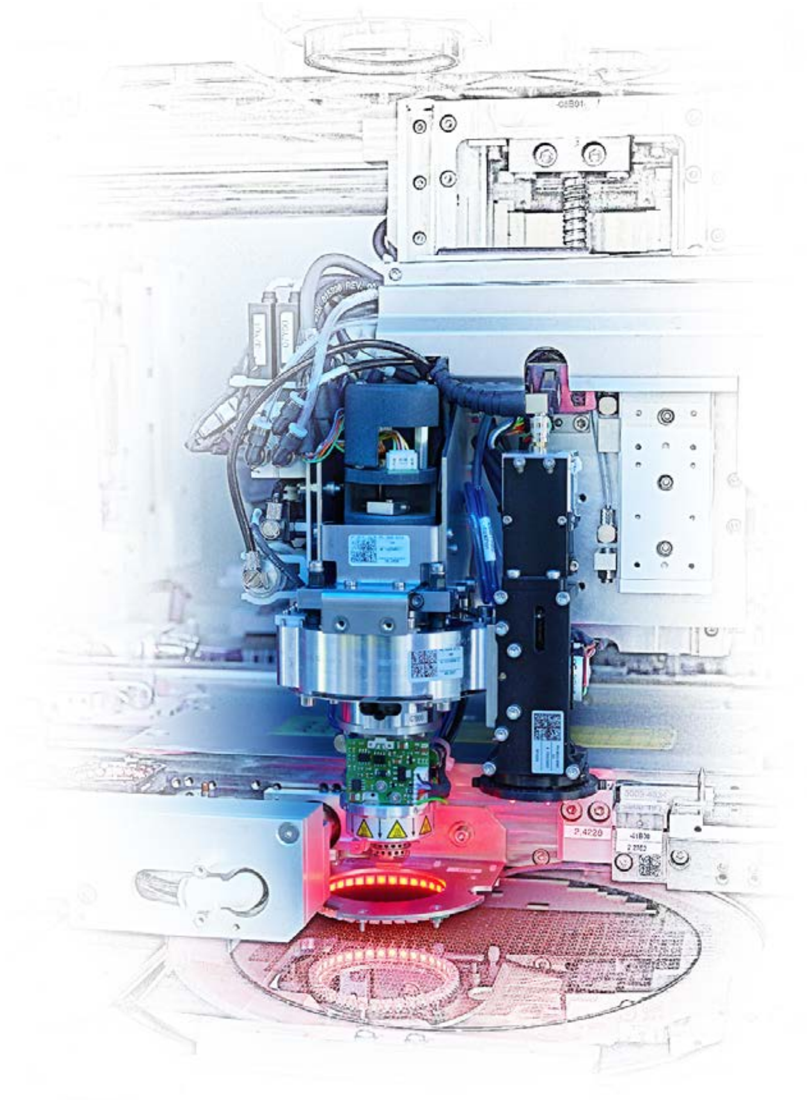
Datacon 2200 evo *hF*

Besi

Advanced Process Capability

- Renewable energy
- e-mobility
- Power transmission



High force bonding

- Bond force 500 N
- Hot bond head
- Closed loop

Sintering

- Sinter film handling
- Sinter paste dispensing
- Pre-applied sinter paste

Heating

- 450 °C tool
- 300 °C substrate

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Performance

- X/Y placement accuracy: ±10 µm@3s
- Theta placement accuracy: ±0,15 °@3s

Bond Heads

- Standard bond head 0 ° - 360 ° rotation
- Heated bond head 450 °C (optional)
- Bond force: 0,5 N – 500 N

Footprint

- LxDxH: 1160 mm x 1225 mm x 1800 mm
- Statistics
- Uptime > 98%
- Yield > 99.95%

Chip Trays

- Waffle pack/Gel-Pak® 2“ x 2“ and 4“ x 4“
- JEDEC tray on request

Substrates and Carriers

- Substrate working range
- 12“ x 7“ (300 mm x 175 mm)
- Substrate heating 350 °C (optional)

Wafer

- Die size die attach: 0,17 mm – 50 mm
- Die thickness: 0,17 mm – 7 mm
- Wafer size: 2“ – 12“ (50 mm – 300 mm)